

Silicon NPN Power Transistors

2SD1380

DESCRIPTION

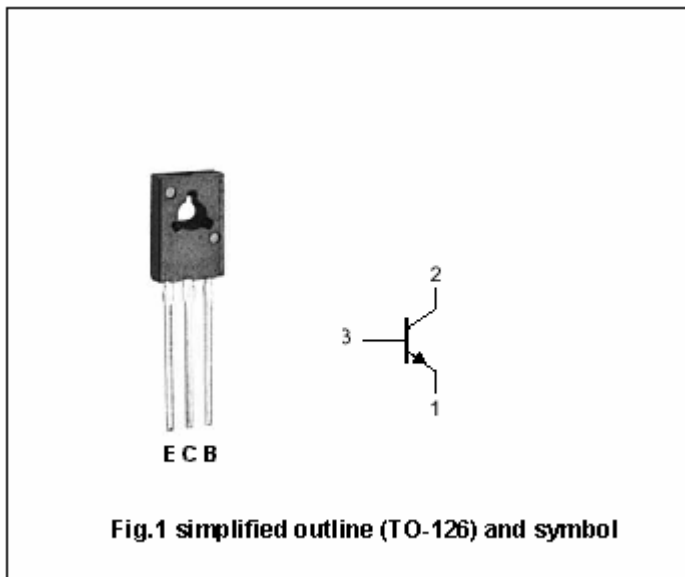
- With TO-126 package
- Complement to type 2SB1009
- Low collector saturation voltage

APPLICATIONS

- For low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	40	V
V _{CEO}	Collector-emitter voltage	Open base	32	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		2	A
P _C	Collector power dissipation	T _C =25°C	10	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =1mA ; I _B =0	32			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =50μA ; I _E =0	40			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =50μA ; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =2.0A ; I _B =0.2A		0.5	0.8	V
I _{CBO}	Collector cut-off current	V _{CB} =20V ; I _E =0			1	μA
I _{EBO}	Emitter cut-off current	V _{EB} =4V ; I _C =0			1	μA
h _{FE}	DC current gain	I _C =0.5A ; V _{CE} =3V	82		390	
f _T	Transition frequency	I _E =-0.5A ; V _{CE} =5V		100		MHz
C _{OB}	Collector output capacitance	I _E =0 ; f=1MHz ; V _{CB} =10V		30		pF

◆ h_{FE} Classifications

P	Q	R
82-180	120-270	180-390

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PACKAGE OUTLINE

